Abstracts

A 12-GHz 1-W GaAs MESFET Amplifier (Dec. 1979 [T-MTT])

M. Nakatani, Y. Kadowaki and T. Ishii. "A 12-GHz 1-W GaAs MESFET Amplifier (Dec. 1979 [T-MTT])." 1979 Transactions on Microwave Theory and Techniques 27.12 (Dec. 1979 [T-MTT] (1979 Symposium Issue)): 1066-1070.

A practical method using small signal S/sub 22/ is presented for the design of GaAs MESFET power amplifier. A five-stage MIC amplifier, which delivers 1-W power output with 27-dB linear gain in the 12-GHz band, was constructed based on this method. Further improvement in the power performance of the amplifier was investigated using newly developed flip-chip MESFET's resulting in 4-W and 2-W power outputs for a unit and a five-stage amplifier, respectively.

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